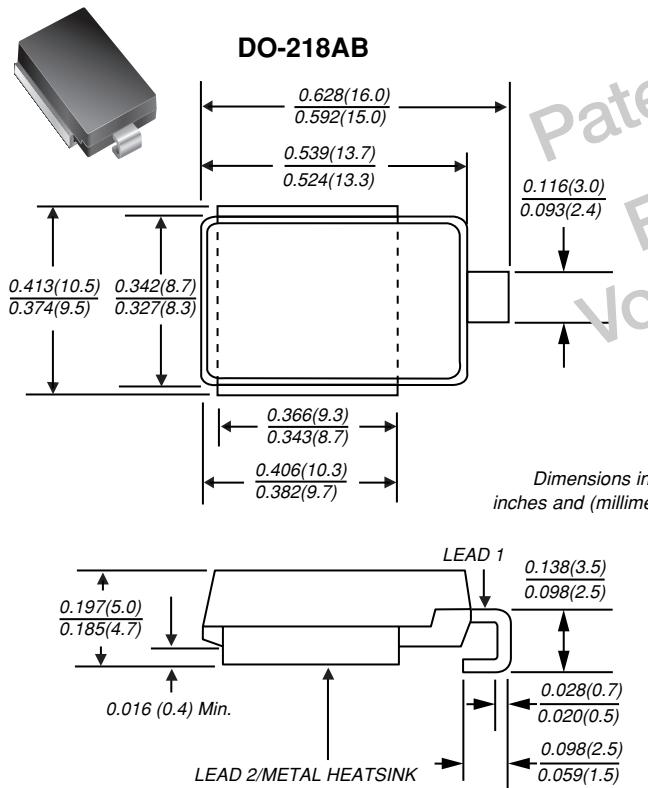
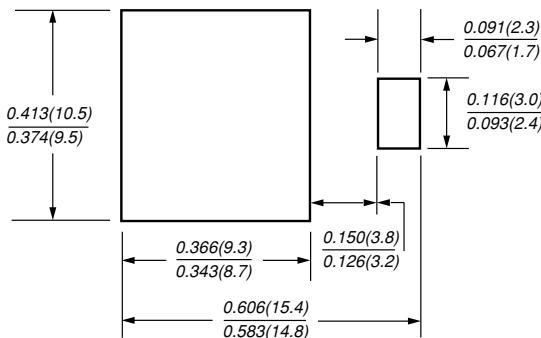


Surface Mount Automotive Transient Voltage Suppressors



Stand-off Voltage 10 to 43V
Peak Pulse Power 6600W (10/1000 μ s)
 5200W (10/10,000 μ s)

Mounting Pad Layout



*Patent #'s:
 4,980,315
 5,166,769
 5,278,095

Features

- Ideally suited for load dump protection
- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- High temperature stability due to unique oxide passivation and patented PAR® construction
- Integrally molded heatsink provides a very low thermal resistance for maximum heat dissipation
- Low leakage current at $T_J = 175^\circ\text{C}$
- High temperature soldering guaranteed: 260°C for 10 seconds at terminals
- Meets ISO7637-2 surge spec.
- Low forward voltage drop

Mechanical Data

Case: Molded plastic body, surface mount with heatsink integrally mounted in the encapsulation

Terminals: Plated, solderable per MIL-STD-750, Method 2026

Polarity: Heatsink is anode

Mounting Position: Any

Weight: 0.091 oz., 2.58 g

Packaging codes/options:

2D/750 per 13" Reel (16mm Tape),
 anode towards sprocket hole, 4.5K/box
 2E/750 per 13" Reel (16mm Tape),
 cathode towards sprocket hole, 4.5K/box

Maximum Ratings and Thermal Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak pulse power dissipation with 10/1000 μ s waveform 10/10,000 μ s waveform	PPPM	6600 5200	W
Steady state power dissipation	P _D	8.0	W
Peak pulse current with a 10/1000 μ s waveform ⁽¹⁾	I _{PPM}	See Table 1	A
Peak forward surge current, 8.3ms single half sine-wave	I _{FSM}	700	A
Typical thermal resistance junction to case	R _{θJC}	0.90	°C/W
Operating junction and storage temperature range	T _J , T _{STG}	-55 to +175	°C

Notes: (1) Non-repetitive current pulse derated above $T_A=25^\circ\text{C}$

SM8S Series

Vishay Semiconductors
formerly General Semiconductor



Electrical Characteristics (Tc = 25°C unless otherwise noted)

Device Type	Breakdown Voltage $V_{(BR)}$ (V)		Test Current I_T (mA)	Stand-off Voltage V_{WM} (V)	Maximum Reverse Leakage at V_{WM} I_D (μ A)	Maximum Reverse Leakage at V_{WM} $T_c = 175^\circ C$ $I_D(\mu A)$	Max. Peak Pulse Current at 10/1000 μ s Waveform (A)	Maximum Clamping Voltage at I_{PPM} V_c (V)
	Min.	Max.						
SM8S10	11.1	13.6	5.0	10	15	250	351	18.8
SM8S10A	11.1	12.3	5.0	10	15	250	388	17.0
SM8S11	12.2	14.9	5.0	11	10	150	328	20.1
SM8S11A	12.2	13.5	5.0	11	10	150	363	18.2
SM8S12	13.3	16.3	5.0	12	10	150	300	22.0
SM8S12A	13.3	14.7	5.0	12	10	150	332	19.9
SM8S13	14.4	17.6	5.0	13	10	150	277	23.8
SM8S13A	14.4	15.9	5.0	13	10	150	307	21.5
SM8S14	15.6	19.1	5.0	14	10	150	256	25.8
SM8S14A	15.6	17.2	5.0	14	10	150	284	23.2
SM8S15	16.7	20.4	5.0	15	10	150	245	26.9
SM8S15A	16.7	18.5	5.0	15	10	150	270	24.4
SM8S16	17.8	21.8	5.0	16	10	150	229	28.8
SM8S16A	17.8	19.7	5.0	16	10	150	254	26.0
SM8S17	18.9	23.1	5.0	17	10	150	216	30.5
SM8S17A	18.9	20.9	5.0	17	10	150	239	27.6
SM8S18	20.0	24.4	5.0	18	10	150	205	32.2
SM8S18A	20.0	22.1	5.0	18	10	150	226	29.2
SM8S20	22.2	27.1	5.0	20	10	150	184	35.8
SM8S20A	22.2	24.5	5.0	20	10	150	204	32.4
SM8S22	24.4	29.8	5.0	22	10	150	168	39.4
SM8S22A	24.4	26.9	5.0	22	10	150	186	35.5
SM8S24	26.7	32.6	5.0	24	10	150	153	43.0
SM8S24A	26.7	29.5	5.0	24	10	150	170	38.9
SM8S26	28.9	35.3	5.0	26	10	150	142	46.6
SM8S26A	28.9	31.9	5.0	26	10	150	157	42.1
SM8S28	31.1	38.0	5.0	28	10	150	132	50.1
SM8S28A	31.1	34.4	5.0	28	10	150	145	45.4
SM8S30	33.3	40.7	5.0	30	10	150	123	53.5
SM8S30A	33.3	36.8	5.0	30	10	150	136	48.4
SM8S33	36.7	44.9	5.0	33	10	150	112	59.0
SM8S33A	36.7	40.6	5.0	33	10	150	124	53.3
SM8S36	40.0	48.9	5.0	36	10	150	103	64.3
SM8S36A	40.0	44.2	5.0	36	10	150	114	58.1
SM8S40	44.4	54.3	5.0	40	10	150	92.4	71.4
SM8S40A	44.4	49.1	5.0	40	10	150	102	64.5
SM8S43	47.8	58.4	5.0	43	10	150	86.0	76.7
SM8S43A	47.8	52.8	5.0	43	10	150	95.1	69.4

Note: For all types maximum VF = 1.8V at IF = 100A measured on 8.3ms single half sine-wave or equivalent square wave, duty cycle = 4 pulses per minute maximum

Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)
